



Description

The HSBB3P20 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

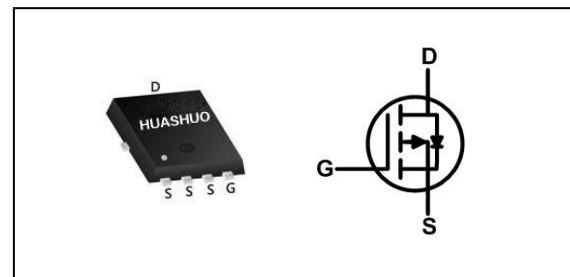
The HSBB3P20 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-200	V
$R_{DS(ON),typ}$	650	m Ω
I_D	-3	A

PRPAK3*3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-200	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-3	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-1.9	A
I_{DM}	Pulsed Drain Current ²	-12	A
EAS	Single Pulse Avalanche Energy ³	81	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	30	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	5	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-200	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-2A	---	650	810	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-2	---	-4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-200V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V, V _{DS} =0V	---	---	± 100	nA
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-2A	---	5.5	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	5.4	---	Ω
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-10V, I _D =-2A	---	82	---	nC
Q _{gs}	Gate-Source Charge		---	19	---	
Q _{gd}	Gate-Drain Charge		---	22	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-50V, V _{GS} =-10V, R _G =3.3Ω, I _D =-2A	---	18	---	ns
T _r	Rise Time		---	4.5	---	
T _{d(off)}	Turn-Off Delay Time		---	49.5	---	
T _f	Fall Time		---	28	---	
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz	---	2155	---	pF
C _{oss}	Output Capacitance		---	49	---	
C _{rss}	Reverse Transfer Capacitance		---	39	---	

Diode Characteristics

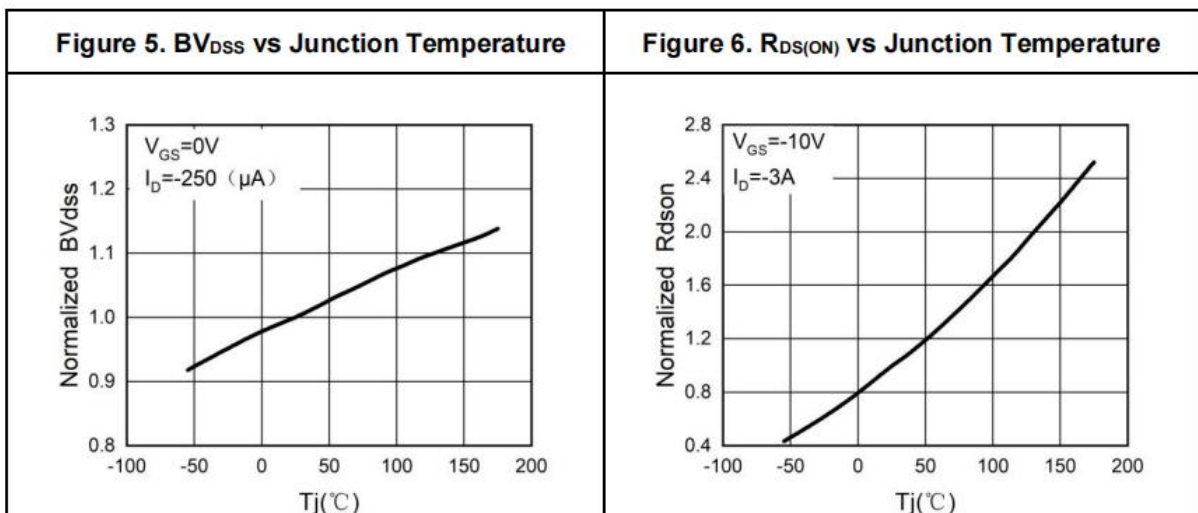
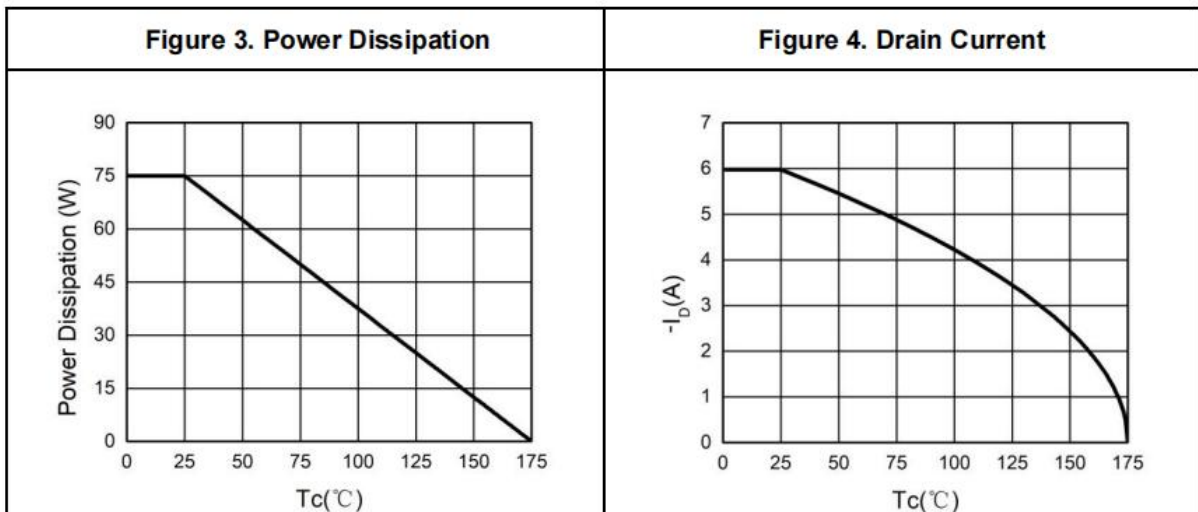
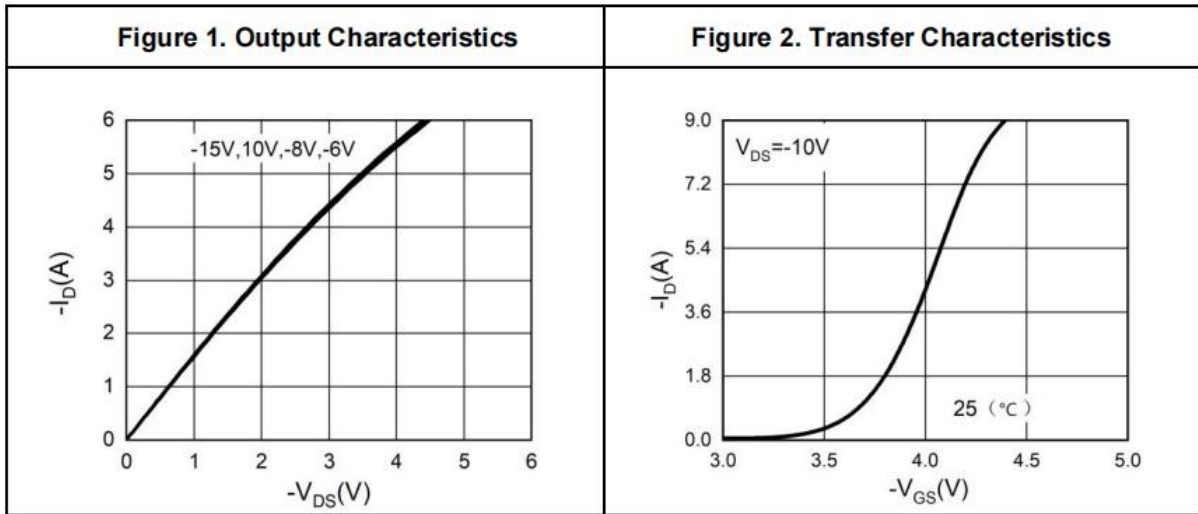
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-3	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-2A, dI/dt=-100A/μs,	---	63	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	195	---	nC

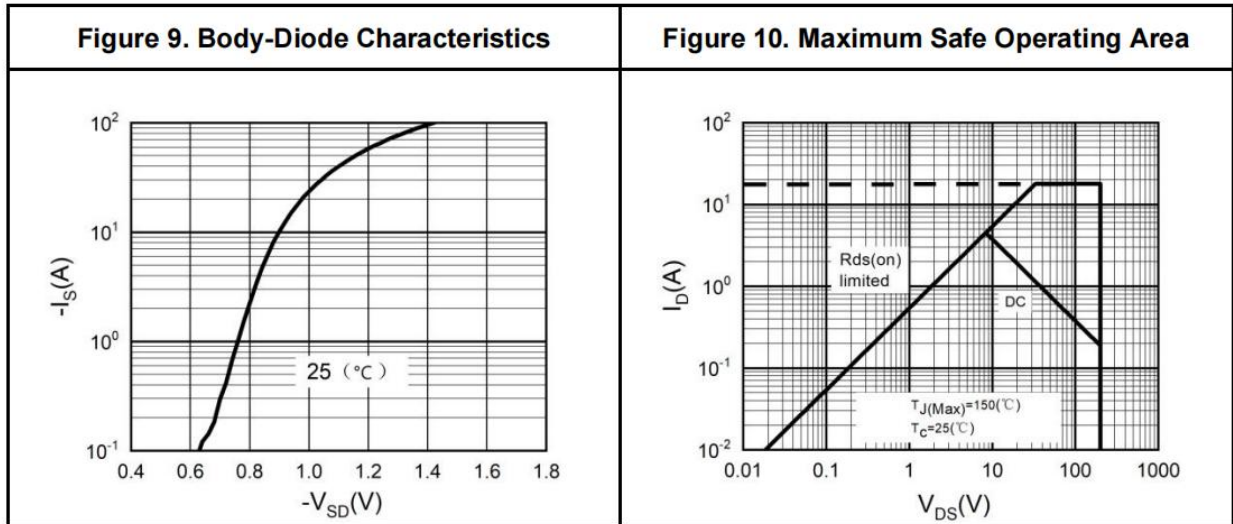
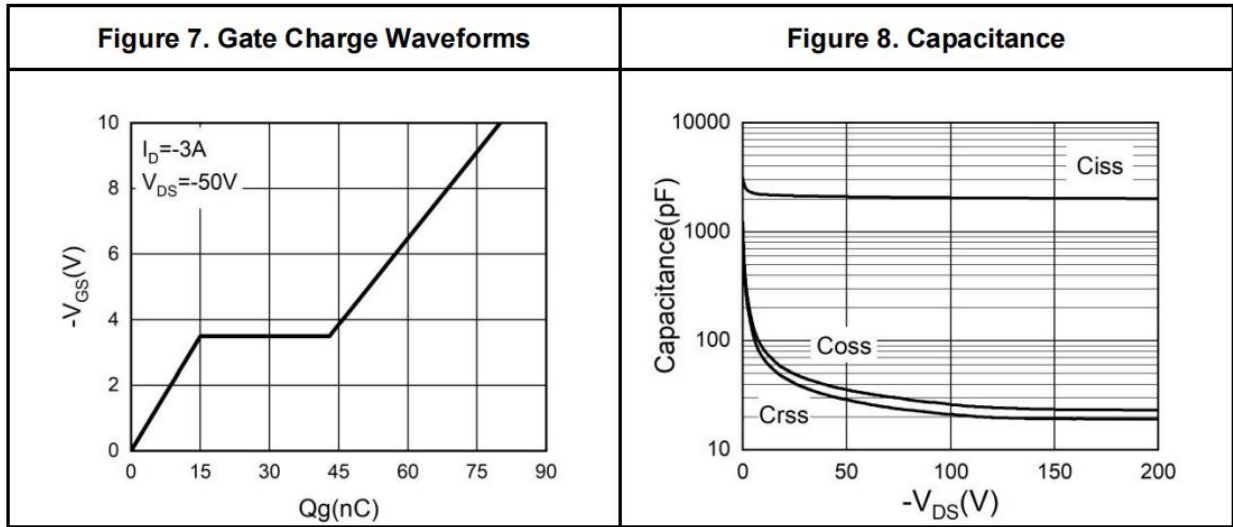
Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

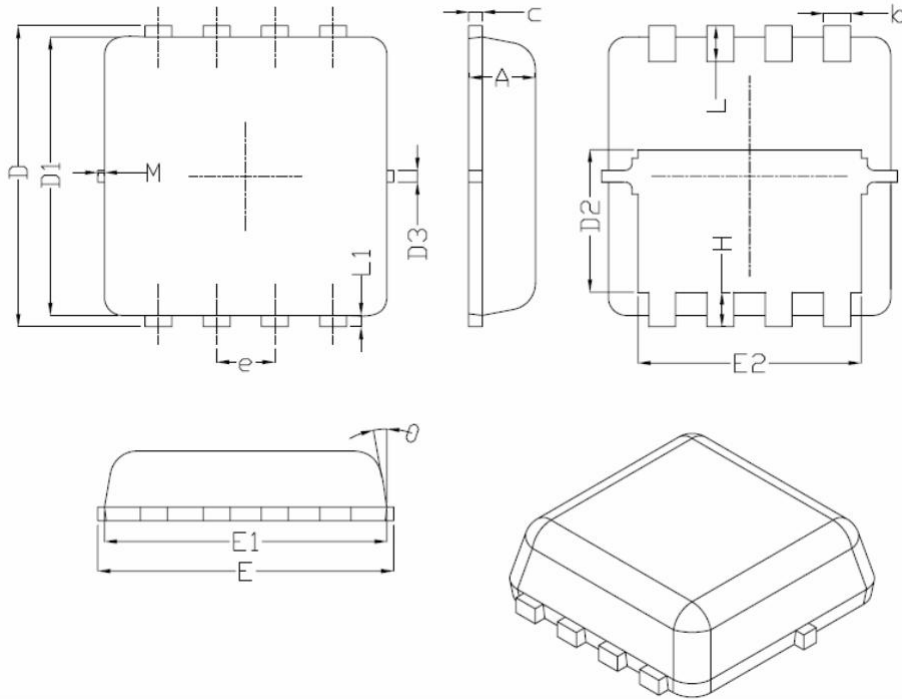






Ordering Information

Part Number	Package code	Packaging
HSBB3P20	PRPAK3*3	3000/Tape&Reel



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.15	3.30	3.45
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°